NTB0101A Auto direction sensing dual supply Rev. 1 — 14 July 2015

Product data sheet

General description 1.

The NTB0101A is a 1-bit, dual supply translating transceiver with auto direction sensing, that enables bidirectional voltage level translation. It consists of two 1-bit I/O ports (A and B), one output enable input (OE) and two supply pins (V_{CC(A)} and V_{CC(B)}). V_{CC(A)} can be supplied at any voltage between 1.2 V and 3.6 V. V_{CC(B)} can be supplied at any voltage between 1.65 V and 5.5 V. This flexibility allows translation between any of the low voltage nodes (1.2 V, 1.5 V, 1.8 V, 2.5 V, 3.3 V and 5.0 V).

Pins A and OE are referenced to V_{CC(A)} and pin B is referenced to V_{CC(B)}. A HIGH level at pin OE causes the outputs to assume a high-impedance OFF-state. This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing damage of the device due to backflow current, when it is powered down.

Features and benefits 2.

- Wide supply voltage range:
 - V_{CC(A)}: 1.2 V to 3.6 V and V_{CC(B)}: 1.65 V to 5.5 V
- I_{OFF} circuitry provides partial power-down mode operation
- Inputs accept voltages up to 5.5 V
- ESD protection:
 - HBM JESD22-A114E Class 2 exceeds 2500 V for port A
 - HBM JESD22-A114E Class 3B exceeds 15000 V for port B
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1500 V
- Latch-up performance exceeds 100 mA per JESD 78B Class II
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



3. Ordering information

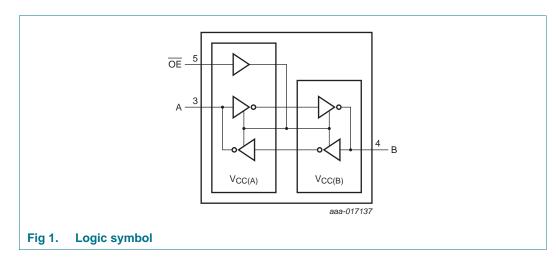
Table 1. Orde	Gable 1. Ordering information								
Type number	Type number Package								
Name		Description	Version						
NTB0101AGW	SC-88	plastic surface-mounted package; 6 leads	SOT363						

4. Marking

Table 2.	Marking codes	
Type num	iber	Marking code ^[1]
NTB0101/	AGW	tL

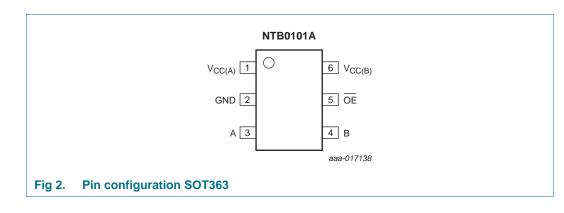
[1] The pin 1 indicator is on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin d	escription		
Symbol	Pin	Description	
V _{CC(A)}	1	supply voltage A	
GND	2	ground (0 V)	
A	3	data input or output (referenced to V _{CC(A)})	
В	4	data input or output (referenced to V _{CC(B)})	
OE	5	output enable input (active LOW; referenced to $V_{CC(A)}$)	
V _{CC(B)}	6	supply voltage B	

7. Functional description

Table 4. Function table^[1]

Supply voltage		Input	Input/output		
V _{CC(A)} V _{CC(B)}		OE	Α	В	
1.2 V to V _{CC(B)}	1.65 V to 5.5 V	Н	Z	Z	
1.2 V to V _{CC(B)}	1.65 V to 5.5 V	L	input or output	output or input	
GND ^[2]	GND ^[2]	Х	Z	Z	

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

[2] When either $V_{CC(A)}$ or $V_{CC(B)}$ is at GND level, the device goes into power-down mode.

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CC(A)}	supply voltage A			-0.5	+6.5	V
V _{CC(B)}	supply voltage B			-0.5	+6.5	V
VI	input voltage		<u>[1]</u>	-0.5	+6.5	V
Vo	output voltage	active mode	[1][2][3]	-0.5	V _{CCO} + 0.5	V
		power-down or 3-state mode	<u>[1]</u>	-0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V		-50	-	mA
I _{OK}	output clamping current	V _O < 0 V		-50	-	mA
lo	output current	$V_{O} = 0 V$ to V_{CCO}	[2]	-	±50	mA
I _{CC}	supply current	I _{CC(A)} or I _{CC(B)}		-	100	mA
I _{GND}	ground current			-100	-	mA
T _{stg}	storage temperature			-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to +125 \ ^{\circ}C$	[4]	-	250	mW

[1] If the input and output current ratings are observed, the minimum input and minimum output voltage ratings may be exceeded.

[2] V_{CCO} is the supply voltage associated with the output.

[3] V_{CCO} + 0.5 V should not exceed 6.5 V.

[4] Above 87.5 °C, the value of P_{tot} derates linearly with 4.0 mW/K.

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Recommended operating conditions 9.

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC(A)}	supply voltage A		1.2	3.6	V
V _{CC(B)}	supply voltage B		1.65	5.5	V
VI	input voltage		0	5.5	V
Vo	output voltage	power-down or 3-state mode; $V_{CC(A)} = 1.2 V \text{ to } 3.6 V;$ $V_{CC(B)} = 1.65 V \text{ to } 5.5 V$			
		port A	0	3.6	V
		port B	0	5.5	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC(A)} = 1.2 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$	-	40	ns/V

[1] The A and B sides of an unused I/O pair must be held in the same state, both at V_{CCI} or GND.

[2] $V_{CC(A)}$ must be less than or equal to $V_{CC(B)}$.

10. Static characteristics

Table 7. **Typical static characteristics**

At recommended operating conditions; $T_{amb} = 25 \ ^{\circ}C$; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OH}	HIGH-level output voltage	port A; $V_{CC(A)}$ = 1.2 V; I_O = -20 μ A	-	1.1	-	V
V _{OL}	LOW-level output voltage	port A; $V_{CC(A)} = 1.2$ V; $I_0 = 20 \ \mu A$	-	0.09	-	V
lı	input leakage current	$\label{eq:OE} \begin{array}{l} \overline{\text{OE}} \text{ input; } V_{\text{I}} = 0 \ \text{V to } 3.6 \ \text{V; } V_{\text{CC}(\text{A})} = 1.2 \ \text{V to } 3.6 \ \text{V; } \\ V_{\text{CC}(\text{B})} = 1.65 \ \text{V to } 5.5 \ \text{V} \end{array}$	-	-	±1	μA
I _{OZ}	OFF-state output current	port A or B; $V_O = 0$ V to V_{CCO} ; $V_{CC(A)} = 1.2$ V to 3.6 V; $V_{CC(B)} = 1.65$ V to 5.5 V	-	-	±1	μA
I _{OFF}	power-off leakage current	port A; V ₁ or V _O = 0 V to 3.6 V; V _{CC(A)} = 0 V; V _{CC(B)} = 0 V to 5.5 V	-	-	±1	μA
		port B; V ₁ or V _O = 0 V to 5.5 V; V _{CC(B)} = 0 V; V _{CC(A)} = 0 V to 3.6 V	-	-	±1	μA
CI	input capacitance	$\overline{\text{OE}}$ input; V _{CC(A)} = 1.2 V to 3.6 V; V _{CC(B)} = 1.65 V to 5.5 V	-	1.0	-	pF
C _{I/O}	input/output	port A; $V_{CC(A)} = 1.2$ V to 3.6 V; $V_{CC(B)} = 1.65$ V to 5.5 V	-	4.0	-	pF
	capacitance	port B; V _{CC(A)} = 1.2 V to 3.6 V; V _{CC(B)} = 1.65 V to 5.5 V	-	7.5	-	pF

[1] V_{CCO} is the supply voltage associated with the output.

Table 8.Typical supply current

At recommended operating conditions; $T_{amb} = 25$ °C; voltages are referenced to GND (ground = 0 V).

V _{CC(A)}	V _{CC(B)}								
	1.8 V		2.5 V	2.5 V		3.3 V		5.0 V	
	I _{CC(A)}	I _{CC(B)}							
1.2 V	10	10	10	10	10	20	10	1050	nA
1.5 V	10	10	10	10	10	10	10	650	nA
1.8 V	10	10	10	10	10	10	10	350	nA
2.5 V	-	-	10	10	10	10	10	40	nA
3.3 V	-	-	-	-	10	10	10	10	nA

Table 9. Static characteristics^[1]

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T _{amb} = -40	°C to +85 °C	$T_{amb} = -40$	Unit	
			Min	Max	Min	Max	
V _{IH}	HIGH-level input voltage	port A or port B and \overline{OE} input; $V_{CC(A)} = 1.2$ V to 3.6 V; $V_{CC(B)} = 1.65$ V to 5.5 V	0.65V _{CCI}	-	0.65V _{CCI}	-	V
VIL	LOW-level input voltage	port A or port B and \overline{OE} input; $V_{CC(A)} = 1.2$ V to 3.6 V; $V_{CC(B)} = 1.65$ V to 5.5 V	-	0.35V _{CCI}	-	0.35V _{CCI}	V
V _{OH} HIGH-level		I _O = -20 μA					
output voltage	port A; $V_{CC(A)} = 1.4$ V to 3.6 V	$V_{CCO}-0.4$	-	$V_{CCO}-0.4$	-	V	
	vollage	port B; $V_{CC(B)}$ = 1.65 V to 5.5 V	$V_{CCO}-0.4$	-	$V_{CCO}-0.4$	-	V
V _{OL} L	LOW-level	I _O = 20 μA					
	output	port A; V _{CC(A)} = 1.4 V to 3.6 V	-	0.4	-	0.4	V
	voltage	port B; $V_{CC(B)} = 1.65$ V to 5.5 V	-	0.4	-	0.4	V
I _I	input leakage current	$\label{eq:cc} \begin{array}{l} \overline{\text{OE}} \text{ input; } V_{\text{I}} = 0 \ \text{V to } 3.6 \ \text{V;} \\ V_{\text{CC}(A)} = 1.2 \ \text{V to } 3.6 \ \text{V;} \\ V_{\text{CC}(B)} = 1.65 \ \text{V to } 5.5 \ \text{V} \end{array}$	-	±2	-	±5	μA
I _{OZ}	OFF-state output current	$\begin{array}{l} \mbox{port A or port B; V_{O} = 0 V or V_{CCO};} \\ V_{CC(A)} = 1.2 V to 3.6 V; \\ V_{CC(B)} = 1.65 V to 5.5 V \end{array}$	-	±2	-	±10	μA
I _{OFF}	power-off leakage	port A; V ₁ or V _O = 0 V to 3.6 V; V _{CC(A)} = 0 V; V _{CC(B)} = 0 V to 5.5 V	-	±2	-	±10	μA
	current	port B; V ₁ or V _O = 0 V to 5.5 V; V _{CC(B)} = 0 V; V _{CC(A)} = 0 V to 3.6 V	-	±2	-	±10	μA

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Symbol	Parameter	Conditions	T _{amb} = -	-40 °C to +85 °C	T _{amb} = -	40 °C to +125 °C	Unit
			Min	Max	Min	Max	
I _{CC}	supply	$V_I = 0 V \text{ or } V_{CCI}; I_O = 0 A$					
	current	I _{CC(A)}					
		OE = HIGH;	-	3	-	15	μA
		$V_{CC(A)} = 1.4 V \text{ to } 3.6 V;$ $V_{CC(B)} = 1.65 V \text{ to } 5.5 V$					
		\overline{OE} = LOW; V _{CC(A)} = 1.4 V to 3.6 V; V _{CC(B)} = 1.65 V to 5.5 V	-	3	-	20	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-	2	-	15	μA
		$V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 5.5 \text{ V}$	-	-2	-	-15	μA
		I _{CC(B)}					
		$\overline{OE} = HIGH;V_{CC(A)} = 1.4 V to 3.6 V;V_{CC(B)} = 1.65 V to 5.5 V$	-	5	-	15	μA
		$\overline{OE} = LOW; V_{CC(A)} = 1.4 V \text{ to } 3.6 V; V_{CC(B)} = 1.65 V \text{ to } 5.5 V$	-	5	-	20	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$	-	-2	-	-15	μA
		$V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 5.5 \text{ V}$	-	2	-	15	μA
		$I_{CC(A)} + I_{CC(B)}$					
		$V_{CC(A)} = 1.4 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$	-	8	-	40	μA

Table 9. Static characteristics^[1] ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

[1] V_{CCI} is the supply voltage associated with the input and V_{CCO} is the supply voltage associated with the output.

11. Dynamic characteristics

Table 10. Typical dynamic characteristics^[1]

Voltages are referenced to GND (ground = 0 V); typical values are measured with $V_{CC(A)} = 1.2$ V and $T_{amb} = 25$ °C; for test circuit, see <u>Figure 5</u>; for waveforms, see <u>Figure 3</u> and <u>Figure 4</u>.

Symbol	Parameter	Conditions	V _{CC(B)}		Unit			
			1.8 V	2.5 V	3.3 V	5.0 V		
t _{pd}	propagation delay	A to B	5.9	4.8	4.4	4.2	ns	
		B to A	5.6	4.8	4.5	4.4	ns	
t _{en}	enable time	OE to A, B	0.5	0.5	0.5	0.5	μS	
t _{dis}	disable time	OE to A; no external load [2]	6.9	6.9	6.9	6.9	ns	
		OE to B; no external load [2]	9.5	8.6	8.5	8.0	ns	
		OE to A	81	69	83	68	ns	
		OE to B	81	69	83	68	ns	
t _t	transition time	port A	4.0	4.0	4.1	4.1	ns	
		port B	2.6	2.0	1.7	1.4	ns	
t _W	pulse width	data inputs	15	13	13	13	ns	
f _{data}	data rate		70	80	80	80	Mbit/s	

[2] Delay between \overline{OE} going HIGH and when the outputs are disabled.

Table 11. Dynamic characteristics for temperature range -40 °C to +85 °C[1]

Voltages are referenced to GND (ground = 0 V); for test circuit, see <u>Figure 5</u>; for waveforms, see <u>Figure 3</u> and <u>Figure 4</u>.

Symbol	Parameter	Conditions	V _{CC(B)}								Unit
				± 0.15 V	2.5 V	± 0.2 V	3.3 V	± 0.3 V	5.0 V :	± 0.5 V	
			Min	Max	Min	Max	Min	Max	Min	Max	_
V _{CC(A)} =	1.5 V ± 0.1 V	1									
t _{pd}	propagation	A to B	1.4	12.9	1.2	10.1	1.1	10.0	0.8	9.9	ns
	delay	B to A	0.9	14.2	0.7	12.0	0.4	11.7	0.3	13.7	ns
t _{en}	enable time	OE to A, B	-	1.0	-	1.0	-	1.0	-	1.0	μS
t _{dis} disa	disable time	OE to A; no external [2] load	1.0	11.9	1.0	11.9	1.0	11.9	1.0	11.9	ns
		OE to B; no external [2] load	1.0	16.9	1.0	15.2	1.0	14.1	1.0	13.8	ns
		OE to A	-	320	-	260	-	260	-	280	ns
		OE to B	-	200	-	200	-	200	-	200	ns
tt	transition	port A	0.9	5.1	0.9	5.1	0.9	5.1	0.9	5.1	ns
	time	port B	0.9	4.7	0.6	3.2	0.5	2.5	0.4	2.7	ns
t _W	pulse width	data inputs	25	-	25	-	25	-	25	-	ns
f _{data}	data rate		-	40	-	40	-	40	-	40	Mbit/s
V _{CC(A)} =	1.8 V ± 0.15 V	1	1								
t _{pd}	propagation	A to B	1.6	11.0	1.4	7.7	1.3	6.8	1.2	6.5	ns
	delay	B to A	1.5	12.0	1.3	8.4	1.0	7.6	0.9	7.1	ns
t _{en}	enable time	OE to A, B	-	1.0	-	1.0	-	1.0	-	1.0	μS
t _{dis}	disable time	OE to A; no external [2] load	1.0	11.0	1.0	11.0	1.0	11.0	1.0	11.0	ns
		OE to B; no external [2] load	1.0	15.4	1.0	13.5	1.0	12.4	1.0	12.1	ns
		OE to A	-	260	-	230	-	230	-	230	ns
		OE to B	-	200	-	200	-	200	-	200	ns
tt	transition	port A	0.8	4.1	0.8	4.1	0.8	4.1	0.8	4.1	ns
	time	port B	0.9	4.7	0.6	3.2	0.5	2.5	0.4	2.7	ns
t _W	pulse width	data inputs	20	-	17	-	17	-	17	-	ns
f _{data}	data rate		-	49	-	60	-	60	-	60	Mbit/s
V _{CC(A)} =	$= 2.5 \text{ V} \pm 0.2 \text{ V}$										
t _{pd}	propagation	A to B	-	-	1.1	6.3	1.0	5.2	0.9	4.7	ns
	delay	B to A	-	-	1.2	6.6	1.1	5.1	0.9	4.4	ns
t _{en}	enable time	OE to A, B	-	-	-	1.0	-	1.0	-	1.0	μS

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Symbol	Parameter	Conditions	V _{CC(B)}								Unit
			1.8 V :	± 0.15 V	2.5 V :	± 0.2 V	3.3 V :	± 0.3 V	5.0 V	± 0.5 V	
			Min	Max	Min	Max	Min	Мах	Min	Мах	_
t _{dis}	disable time	OE to A; no external	-	-	1.0	9.2	1.0	9.2	1.0	9.2	ns
		OE to B; no external [2] load	-	-	1.0	11.9	1.0	10.7	1.0	10.2	ns
		OE to A	-	-	-	200	-	200	-	200	ns
		OE to B	-	-	-	200	-	200	-	200	ns
t _t transition		port A	-	-	0.7	3.0	0.7	3.0	0.7	3.0	ns
time	port B	-	-	0.7	3.2	0.5	2.5	0.4	2.7	ns	
t _W	pulse width	data inputs	-	-	12	-	10	-	10	-	ns
f _{data}	data rate		-	-	-	85	-	100	-	100	Mbit/s
$V_{CC(A)} =$	3.3 V ± 0.3 V	1									
t _{pd}	propagation	A to B	-	-	-	-	0.9	4.7	0.8	4.0	ns
	delay	B to A	-	-	-	-	1.0	4.9	0.9	3.8	ns
t _{en}	enable time	OE to A, B	-	-	-	-	-	1.0	-	1.0	μs
t _{dis}	disable time	OE to A; no external [2] load	-	-	-	-	1.0	9.2	1.0	9.2	ns
		OE to B; no external [2] load	-	-	-	-	1.0	10.1	1.0	9.6	ns
		OE to A	-	-	-	-	-	260	-	260	ns
		OE to B	-	-	-	-	-	200	-	200	ns
t _t	transition	port A	-	-	-	-	0.7	2.5	0.7	2.5	ns
	time	port B	-	-	-	-	0.5	2.5	0.4	2.7	ns
t _W	pulse width	data inputs	-	-	-	-	10	-	10	-	ns
f _{data}	data rate		-	-	-	-	-	100	-	100	Mbit/s

Table 11. Dynamic characteristics for temperature range $-40 \text{ °C to } +85 \text{ °C} \frac{[1]}{\dots}$ continued Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 5; for waveforms, see Figure 3 and Figure 4.

[1] t_{pd} is the same as t_{PLH} and t_{PHL} . t_{en} is the same as t_{PZL} and t_{PZH} . t_{dis} is the same as t_{PLZ} and t_{PHZ} .

 t_{t} is the same as t_{THL} and $t_{TLH}.$

[2] Delay between \overline{OE} going HIGH and when the outputs are disabled.

Table 12. Dynamic characteristics for temperature range –40 °C to +125 °C^[1]

Voltages are referenced to GND (ground = 0 V); for test circuit, see Figure 5; for waveforms, see Figure 3 and Figure 4.

Symbol Para	Parameter	Conditions	V _{CC(B}	V _{CC(B)}							
			1.8 V	$1.8~V\pm 0.15~V~~2.5$		2.5 V ± 0.2 V		$3.3~V\pm0.3~V$		$5.0 \text{ V} \pm 0.5 \text{ V}$	
			Min	Max	Min	Max	Min	Max	Min	Max	
V _{CC(A)} =	1.5 V ± 0.1 V		i								
t _{pd}	propagation	A to B	1.4	15.9	1.2	13.1	1.1	13.0	0.8	12.9	ns
	delay	B to A	0.9	17.2	0.7	15.0	0.4	14.7	0.3	16.7	ns
t _{en}	enable time	OE to A, B	-	1.0	-	1.0	-	1.0	-	1.0	μs

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Symbol	Parameter	Conditions		V _{CC(B})							Unit
				1.8 V	± 0.15 V	2.5 V	± 0.2 V	3.3 V	± 0.3 V	5.0 V	± 0.5 V	_
				Min	Max	Min	Max	Min	Max	Min	Max	_
t _{dis}	disable time	OE to A; no external load	[2]	1.0	12.5	1.0	12.5	1.0	12.5	1.0	12.5	ns
		OE to B; no external load	[2]	1.0	18.1	1.0	16.2	1.0	14.9	1.0	14.6	ns
		OE to A		-	340	-	280	-	280	-	300	ns
		OE to B		-	220	-	220	-	220	-	220	ns
t	transition	port A		0.9	7.1	0.9	7.1	0.9	7.1	0.9	7.1	ns
	time	port B		0.9	6.5	0.6	5.2	0.5	4.8	0.4	4.7	ns
t _W	pulse width	data inputs		25	-	25	-	25	-	25	-	ns
f _{data}	data rate			-	40	-	40	-	40	-	40	Mbit/s
$V_{CC(A)} =$	1.8 V ± 0.15 V											
t _{pd}	propagation	A to B		1.6	14.0	1.4	10.7	1.3	9.8	1.2	9.5	ns
-	delay	B to A		1.5	15.0	1.3	11.4	1.0	10.6	0.9	10.1	ns
t _{en}	enable time	OE to A, B		-	1.0	-	1.0	-	1.0	-	1.0	μS
t _{dis}	disable time	OE to A; no external load	[2]	1.0	11.5	1.0	11.5	1.0	11.5	1.0	11.5	ns
		OE to B; no external load	[2]	1.0	16.5	1.0	14.5	1.0	13.3	1.0	12.7	ns
		OE to A		-	280	-	250	-	250	-	250	ns
		OE to B		-	220	-	220	-	220	-	220	ns
t _t	transition	port A		0.8	6.2	0.8	6.1	0.8	6.1	0.8	6.1	ns
	time	port B		0.9	5.8	0.6	5.2	0.5	4.8	0.4	4.7	ns
t _W	pulse width	data inputs		22	-	19	-	19	-	19	-	ns
f _{data}	data rate			-	45	-	55	-	55	-	55	Mbit/s
$V_{CC(A)} =$	2.5 V ± 0.2 V	1										
t _{pd}	propagation	A to B		-	-	1.1	9.3	1.0	8.2	0.9	7.7	ns
	delay	B to A		-	-	1.2	9.6	1.1	8.1	0.9	7.4	ns
t _{en}	enable time	OE to A, B		-	-	-	1.0	-	1.0	-	1.0	μs
t _{dis}	disable time	OE to A; no external load	[2]	-	-	1.0	9.6	1.0	9.6	1.0	9.6	ns
		OE to B; no external load	[2]	-	-	1.0	12.6	1.0	11.4	1.0	10.8	ns
		OE to A		-	-	-	220	-	220	-	220	ns
		OE to B		-	-	-	220	-	220	-	220	ns
t _t	transition	port A		-	-	0.7	5.0	0.7	5.0	0.7	5.0	ns
	time	port B		-	-	0.7	4.6	0.5	4.8	0.4	4.7	ns
tw	pulse width	data inputs		-	-	14	-	13	-	10	-	ns
data	data rate			-	-	-	75	-	80	-	100	Mbit/s
	3.3 V ± 0.3 V			1						1		
pd	propagation	A to B		-	-	-	-	0.9	7.7	0.8	7.0	ns
	delay	B to A		-	-	-	-	1.0	7.9	0.9	6.8	ns
t _{en}	enable time	OE to A, B		-	-	-	-	-	1.0	-	1.0	μS

Table 12.	Dynamic characteristics for temperature range -40 °C to +125 °C[1]continued
Voltages a	re referenced to GND (around = $0 V$); for test circuit, see Figure 5; for waveforms, see Figure 3 and Figure

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Symbol	Parameter	Conditions	V _{CC(B)}								Unit
			$1.8 V \pm 0.15 V$		$2.5 V \pm 0.2 V$		$3.3 V \pm 0.3 V$		$5.0 V \pm 0.5 V$		
			Min	Max	Min	Max	Min	Max	Min	Max	
t _{dis}	disable time	OE to A; no external load [2]	-	-	-	-	1.0	9.5	1.0	9.5	ns
		OE to B; no external load [2]	-	-	-	-	1.0	10.7	1.0	9.6	ns
		OE to A	-	-	-	-	-	280	-	280	ns
		OE to B	-	-	-	-	-	220	-	220	ns
t _t	transition	port A	-	-	-	-	0.7	4.5	0.7	4.5	ns
	time	port B	-	-	-	-	0.5	4.1	0.4	4.7	ns
t _W	pulse width	data inputs	-	-	-	-	10	-	10	-	ns
f _{data}	data rate		-	-	-	-	-	100	-	100	Mbit/s

Table 12. Dynamic characteristics for temperature range –40 °C to +125 °C[1] ... continued

Voltages are referenced to GND (ground = 0 V); for test circuit, see <u>Figure 5</u>; for waveforms, see <u>Figure 3</u> and <u>Figure 4</u>.

 $\label{eq:tpd} [1] \quad t_{pd} \text{ is the same as } t_{PLH} \text{ and } t_{PHL}.$

 $t_{en} \mbox{ is the same as } t_{PZL} \mbox{ and } t_{PZH}.$

 t_{dis} is the same as t_{PLZ} and $t_{\text{PHZ}}.$

 t_t is the same as t_{THL} and $t_{\text{TLH.}}$

[2] Delay between \overline{OE} going HIGH and when the outputs are disabled.

Table 13. Typical power dissipation capacitance table

Tested at $T_{amb} = 25 \ ^{\circ}C$; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	V _{CC(A)}							Unit	
			1.2 V	1.2 V	1.5 V	1.8 V	2.5 V	2.5 V	3.3 V		
			V _{CC(B)}								
			1.8 V	5.0 V	1.8 V	1.8 V	2.5 V	5.0 V	3.3 V to 5.0 V		
C _{PD} power		outputs enabled; $\overline{OE} = GND$									
	dissipation	port A: (direction A to B)	5	5	5	5	5	5	5	pF	
	capacitance	port A: (direction B to A)	8	8	8	8	8	8	8	pF	
		port B: (direction A to B)	18	18	18	18	18	18	18	pF	
		port B: (direction B to A)	13	16	12	12	12	12	13	pF	
		outputs disabled; $\overline{OE} = V_{CC(A)}$									
		port A: (direction A to B)	0.12	0.12	0.04	0.05	0.08	0.08	0.07	pF	
		port A: (direction B to A)	0.01	0.01	0.01	0.01	0.01	0.01	0.01	pF	
		port B: (direction A to B)	0.01	0.01	0.01	0.01	0.01	0.01	0.01	pF	
		port B: (direction B to A)	0.07	0.09	0.07	0.07	0.05	0.09	0.09	pF	

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

 $\mathsf{P}_{\mathsf{D}} = \mathsf{C}_{\mathsf{P}\mathsf{D}} \times \mathsf{V}_{\mathsf{C}\mathsf{C}}{}^2 \times \mathsf{f}_i \times \mathsf{N} + \Sigma(\mathsf{C}_{\mathsf{L}} \times \mathsf{V}_{\mathsf{C}\mathsf{C}}{}^2 \times \mathsf{f}_{\mathsf{o}}) \text{ where:}$

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

 C_L = load capacitance in pF;

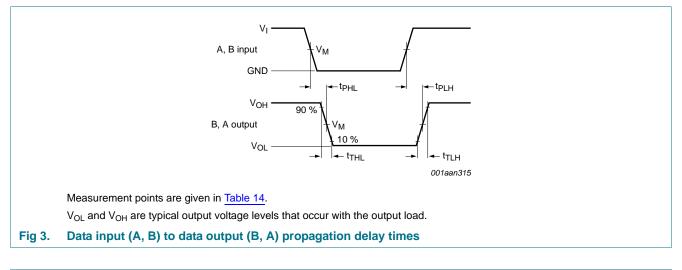
V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$ = sum of the outputs.

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12. Waveforms



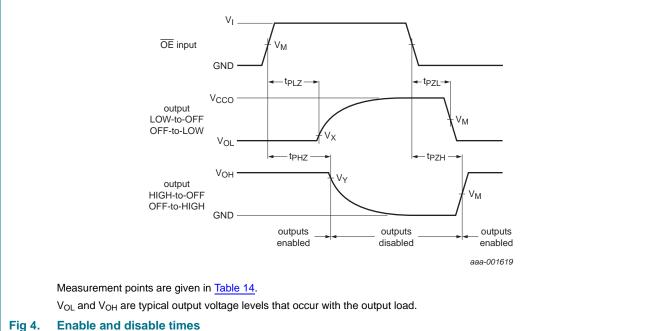


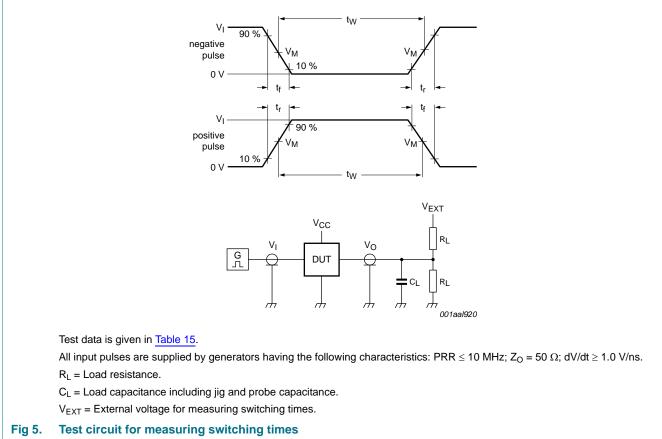
Table 14. Measurement points^[1]

Supply voltage	Input	Output		
V _{cco}	V _M	V _M	V _X	V _Y
1.2 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.1 V	V _{OH} – 0.1 V
$1.5~V\pm0.1~V$	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.1 V	V _{OH} – 0.1 V
$1.8~V\pm0.15~V$	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	V _{OH} – 0.15 V
$2.5~\text{V}\pm0.2~\text{V}$	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	V _{OH} – 0.15 V
$3.3~\text{V}\pm0.3~\text{V}$	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	V _{OH} – 0.3 V
$5.0~\text{V}\pm0.5~\text{V}$	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	V _{OH} – 0.3 V

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[1] V_{CCI} is the supply voltage associated with the input and V_{CCO} is the supply voltage associated with the output.

Table 15. Test data

Supply voltage		Input		Load		V _{EXT}			
V _{CC(A)}	V _{CC(B)}	V <mark>[1]</mark>	∆t/∆V	C∟	RL ^[2]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ} [3]	
1.2 V to 3.6 V	1.65 V to 5.5 V	V _{CCI}	\leq 1.0 ns/V	15 pF	50 kΩ, 1 MΩ	open	open	2V _{CCO}	

[1] V_{CCI} is the supply voltage associated with the input.

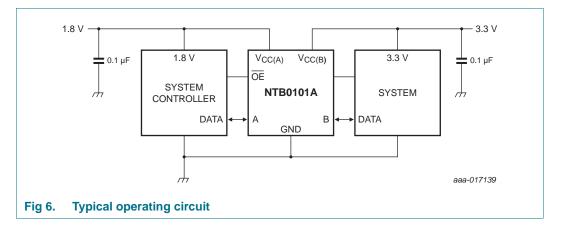
[2] For measuring data rate, pulse width, propagation delay and output rise and fall measurements, $R_L = 1 M\Omega$. For measuring enable and disable times, $R_L = 50 k\Omega$.

[3] V_{CCO} is the supply voltage associated with the output.

13. Application information

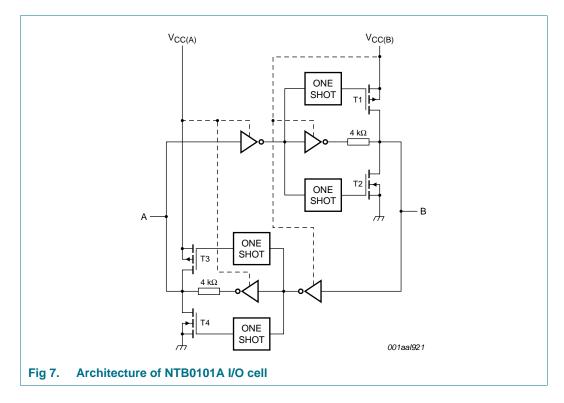
13.1 Applications

Voltage level-translation applications. The NTB0101A can be used to interface between devices or systems operating at different supply voltages. See <u>Figure 6</u> for a typical operating circuit using the NTB0101A.



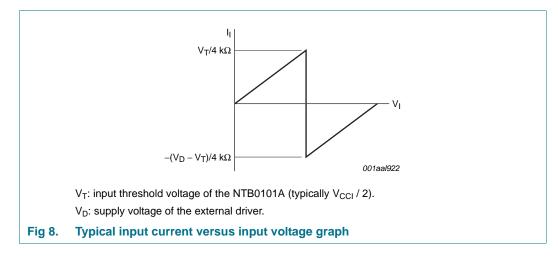
13.2 Architecture

The architecture of the NTB0101A is shown in Figure 7. The device does not require an extra input signal to control the direction of data flow from A to B or from B to A. In a static state, the output drivers of the NTB0101A can maintain a defined output level, but the output architecture is weak, so that they can be overdriven by an external driver when data on the bus starts flowing in the opposite direction. The output of one-shot circuits detect rising or falling edges on the ports A or B. During a rising edge, the one-shot circuits turn on the PMOS transistors (T1, T3) for a short duration, accelerating the LOW-to-HIGH transition. Similarly, during a falling edge, the one-shot circuits turn on the NMOS transistors (T2, T4) for a short duration, accelerating the HIGH-to-LOW transition. During output transitions, the typical output impedance is 70 Ω at V_{CCO} = 1.2 V to 1.8 V. It is 50 Ω at V_{CCO} = 1.8 V to 3.3 V and 40 Ω at V_{CCO} = 3.3 V to 5.0 V.



13.3 Input driver requirements

For correct operation, the device that drives the data I/Os of the NTB0101A must have a minimum drive capability of ± 2 mA. See <u>Figure 8</u> for a plot of typical input current versus input voltage.



13.4 Power-up

 $V_{CC(A)}$ must never be higher than $V_{CC(B)}$ during operation. However during power-up, $V_{CC(A)} \ge V_{CC(B)}$ does not damage the device. Either of the power supplies can be ramped up first and hence no special power-up sequencing is required. The NTB0101A includes circuitry that disables all output ports when either $V_{CC(A)}$ or $V_{CC(B)}$ is switched off.

13.5 Enable and disable

An output enable input (\overline{OE}) is used to disable the device. Setting \overline{OE} = HIGH causes all I/Os to assume the high-impedance OFF-state. The disable time (t_{dis} with no external load) indicates the delay between when \overline{OE} goes HIGH and when outputs actually become disabled. The enable time (t_{en}) indicates the amount of time the user must allow for a one-shot circuitry to become operational after \overline{OE} is taken LOW. To ensure a high-impedance OFF-state during power-up or power-down, pin \overline{OE} should be tied to $V_{CC(A)}$ through a pull-up resistor. The minimum value of the resistor determines the current-sourcing capability of the driver.

13.6 Pull-up or pull-down resistors on I/O lines

As mentioned previously, the NTB0101A is designed with low static drive strength to drive capacitive loads of up to 70 pF. To avoid output contention issues, all pull-up or pull-down resistors used, must be above 50 k Ω . For this reason, NTB0101A is not recommended for use in open-drain driver applications such as 1-Wire or I²C-bus. For these applications, the NTS0101 level translator is recommended.

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14. Package outline

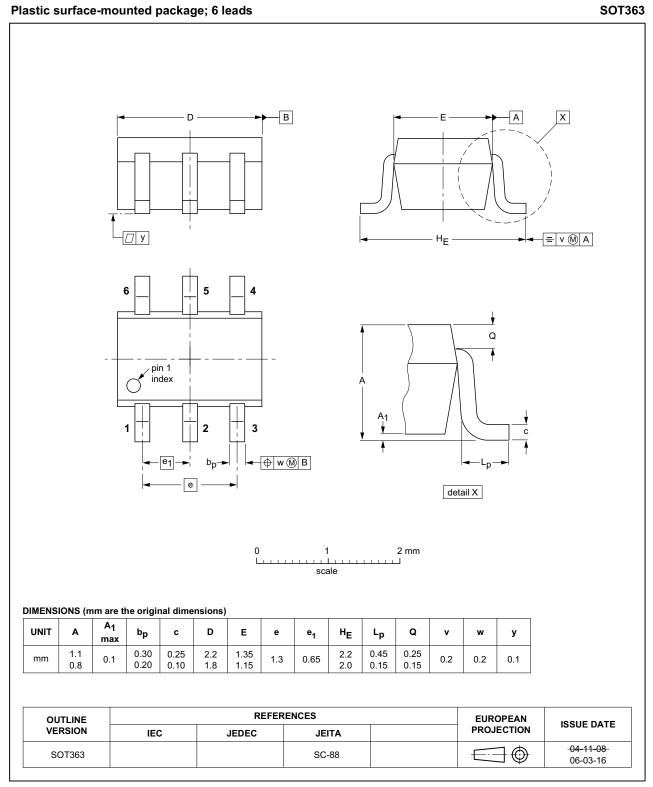


Fig 9. Package outline SOT363 (SC-88)

15. Abbreviations

Table 16. Abbre	Table 16. Abbreviations					
Acronym	Description					
CDM	Charged Device Model					
DUT	Device Under Test					
ESD	ElectroStatic Discharge					
НВМ	Human Body Model					
MM	Machine Model					
NMOS	N-type Metal Oxide Semiconductor					
PMOS	P-type Metal Oxide Semiconductor					
PRR	Pulse Repetition Rate					

16. Revision history

Table 17. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NTB0101A v.1	20150714	Product data sheet	-	-

17. Legal information

17.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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